

DG406, DG407

Single 16-Channel/Differential 8-Channel, CMOS Analog Multiplexers

August 1997

Features

- ON-Resistance (Max).....100Ω
- Low Power Consumption (P_D) <1.2mW
- Fast Transition Time (Max) 300ns
- Low Charge Injection
- TTL, CMOS Compatible
- Single or Split Supply Operation

Applications

- Battery Operated Systems
- Data Acquisition
- Medical Instrumentation
- Hi-Rel Systems
- Communication Systems
- Automatic Test Equipment

Ordering Information

PART NUMBER	TEMP. RANGE (°C)	PACKAGE	PKG. NO.
DG406DJ	-40 to 85	28 Ld PDIP	E28.6
DG406DY	-40 to 85	28 Ld SOIC	M28.3
DG406EJ (Note)	-40 to 85	28 Ld PDIP	E28.6
DG406EY (Note)	-40 to 85	28 Ld SOIC	M28.3
DG406DN	-40 to 85	28 Ld PLCC	N28.45
DG407DJ	-40 to 85	28 Ld PDIP	E28.6
DG407DY	-40 to 85	28 Ld SOIC	M28.3
DG407EJ (Note)	-40 to 85	28 Ld PDIP	E28.6
DG407EY (Note)	-40 to 85	28 Ld SOIC	M28.3
DG407DN	-40 to 85	28 Ld PLCC	N28.45

NOTE: Extended Processing Flow

Description

The DG406 and DG407 monolithic CMOS analog multiplexers are drop-in replacements for the popular DG506A and DG507A series devices. They each include an array of sixteen analog switches, a TTL and CMOS compatible digital decode circuit for channel selection, a voltage reference for logic thresholds, and an ENABLE input for device selection when several multiplexers are present.

These multiplexers feature lower signal ON resistance (<100Ω) and faster transition time ($t_{TRANS} < 300ns$) compared to the DG506A and DG507A. Charge injection has been reduced, simplifying sample and hold applications.

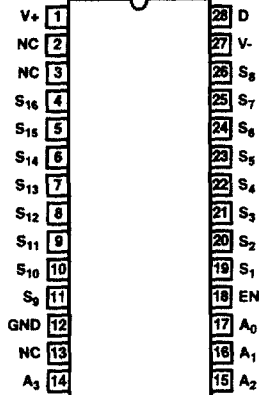
The improvements in the DG406 series are made possible by using a high voltage silicon-gate process. An epitaxial layer prevents the latch-up associated with older CMOS technologies. The 44V maximum voltage range permits controlling 30V_{p-p} signals when operating with ±15V power supplies.

The sixteen switches are bilateral, equally matched for AC or bidirectional signals. The ON resistance variation with analog signals is quite low over a ±5V analog input range.

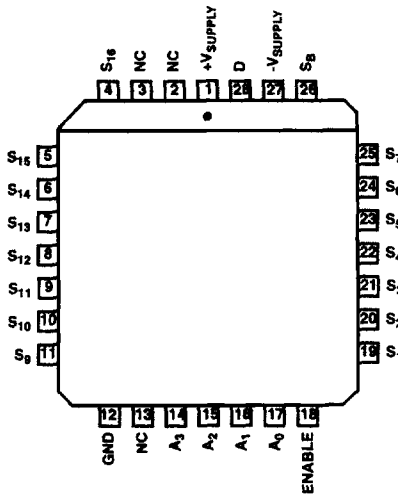
DG406, DG407

Pinouts

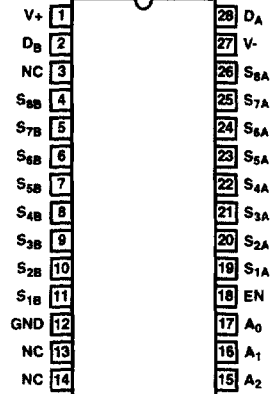
DG406 (PDIP, SOIC)
TOP VIEW



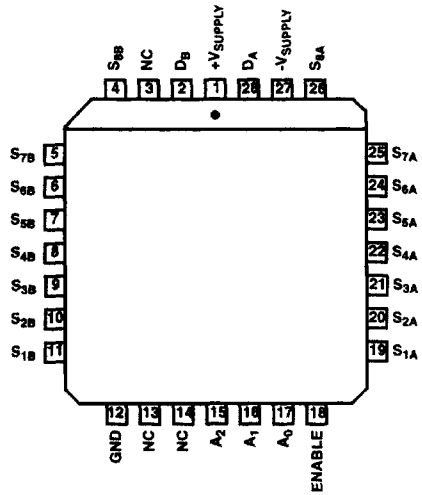
DG406 (PLCC)
TOP VIEW



DG407 (PDIP, SOIC)
TOP VIEW

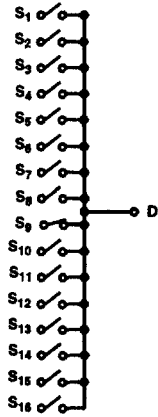


DG407 (PLCC)
TOP VIEW

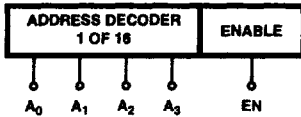


Functional Block Diagrams

DG406



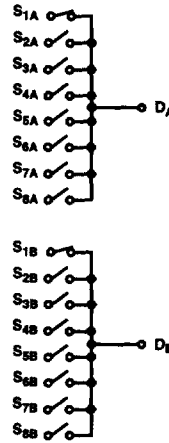
TO DECODER LOGIC
CONTROLLING BOTH
TIERS OF MUXING



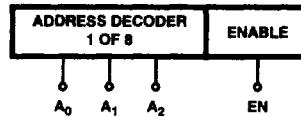
DG406 TRUTH TABLE

A ₃	A ₂	A ₁	A ₀	EN	ON SWITCH
X	X	X	X	0	None
0	0	0	0	1	1
0	0	0	1	1	2
0	0	1	0	1	3
0	0	1	1	1	4
0	1	0	0	1	5
0	1	0	1	1	6
0	1	1	0	1	7
0	1	1	1	1	8
1	0	0	0	1	9
1	0	0	1	1	10
1	0	1	0	1	11
1	0	1	1	1	12
1	1	0	0	1	13
1	1	0	1	1	14
1	1	1	0	1	15
1	1	1	1	1	16

DG407



TO DECODER LOGIC
CONTROLLING BOTH
TIERS OF MUXING



DG407 TRUTH TABLE

A ₂	A ₁	A ₀	EN	ON SWITCH PAIR
X	X	X	0	None
0	0	0	1	1
0	0	1	1	2
0	1	0	1	3
0	1	1	1	4
1	0	0	1	5
1	0	1	1	6
1	1	0	1	7
1	1	1	1	8

Logic "0" = V_{AL} < 0.8V
Logic "1" = V_{AH} > 2.4V
X = Don't Care

DG406, DG407

Absolute Maximum Ratings

Voltages Referenced to V-	
V+	+44.0V
GND	25V
Digital Inputs, V _S , V _D (Note 1)	(V-) -2V to (V+) +2V or 20mA, Whichever Occurs First
Current (Any Terminal)	30mA
Peak Current, S or D (Pulsed 1ms, 10% Duty Cycle Max)	100mA

Thermal Information

Thermal Resistance (Typical, Note 2)	θ_{JA} (°C/W)
PDIP Package	60
SOIC Package	75
PLCC Package	65
Maximum Junction Temperature	150°C
Maximum Storage Temperature Range	-65°C to 150°C
Maximum Lead Temperature (Soldering 10s) (PLCC and SOIC - Lead Tips Only)	300°C

Operating Conditions

Temperature Range -40°C to 85°C

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

NOTES:

1. Signals on S_X, D_X or IN_X exceeding V+ or V- will be clamped by internal diodes. Limit forward diode current to maximum current ratings.
2. θ_{JA} is measured with the component mounted on an evaluation PC board in free air.

Electrical Specifications Test Conditions: V+ = +15V, V- = -15V, V_{AL} = 0.8V, V_{AH} = 2.4V Unless Otherwise Specified

PARAMETER	TEST CONDITIONS	(NOTE 3) TEMP	D SUFFIX 40°C TO 85°C			UNITS
			(NOTE 4) MIN	(NOTE 5) TYP	(NOTE 4) MAX	
ANALOG SWITCH						
Drain-Source ON Resistance, r _{DS(ON)}	V _D = ±10V, I _S = ±10mA (Note 6)	Room	-	50	100	Ω
		Full	-	-	125	Ω
r _{DS(ON)} Matching Between Channels, Δr _{DS(ON)}	V _D = 10V, -10V (Note 7)	Room	-	5	-	%
Source OFF Leakage Current, I _{S(OFF)}	V _{EN} = 0V, V _S = ±10V, V _D = ±10V	Room	-0.5	0.01	0.5	nA
		Full	-5	-	5	nA
Drain OFF Leakage Current, I _{D(OFF)}	DG406	Room	-1	0.04	1	nA
		Full	-40	-	40	nA
		Room	-1	0.04	1	nA
		Full	-20	-	20	nA
Drain ON Leakage Current, I _{D(ON)}	V _S = V _D = ±10V (Note 6)	Room	-1	0.04	1	nA
		Full	-40	-	40	nA
		Room	-1	0.04	1	nA
		Full	-20	-	20	nA
DG407	DG407	Room	-1	0.04	1	nA
		Full	-20	-	20	nA
		Room	-1	0.04	1	nA
		Full	-20	-	20	nA
DIGITAL CONTROL						
Logic High Input Voltage, V _{INH}		Full	2.4	-	-	V
Logic Low Input Voltage, V _{INL}		Full	-	-	0.8	V
Logic High Input Current, I _{AH}	V _A = 2.4V, 15V	Full	-1	-	1	μA
Logic Low Input Current, I _{AL}	V _{EN} = 0V, 2.4V, V _A = 0V	Full	-1	-	1	μA
Logic Input Capacitance, C _{IN}	f = 1MHz	Room	-	7	-	pF

DG406, DG407

Electrical Specifications Test Conditions: $V_+ = +15V$, $V_- = -15V$, $V_{AL} = 0.8V$, $V_{AH} = 2.4V$ Unless Otherwise Specified (Continued)

PARAMETER	TEST CONDITIONS	(NOTE 3) TEMP	D SUFFIX 40°C TO 85°C			UNITS
			(NOTE 4) MIN	(NOTE 5) TYP	(NOTE 4) MAX	
DYNAMIC CHARACTERISTICS						
Transition Time, t_{TRANS}	(See Figure 1)	Room	-	200	300	ns
		Full	-	-	400	ns
Break-Before-Make Interval, t_{OPEN}	(See Figure 3)	Room	25	50	-	ns
		Full	10	-	-	ns
Enable Turn-ON Time, $t_{ON(EN)}$	(See Figure 2)	Room	-	150	200	ns
		Full	-	-	400	ns
Enable Turn-OFF Time, $t_{OFF(EN)}$		Room	-	70	150	ns
		Full	-	-	300	ns
Charge Injection, Q	$C_L = 1nF$, $V_S = 0V$, $R_S = 0\Omega$	Room	-	40	-	pC
OFF Isolation, OIRR	$V_{EN} = 0V$, $R_L = 1k\Omega$, $f = 100kHz$ (Note 8)	Room	-	-69	-	dB
Source OFF Capacitance, $C_{S(OFF)}$	$V_{EN} = 0V$, $V_S = 0V$, $f = 1MHz$	Room	-	8	-	pF
Drain OFF Capacitance, $C_{D(OFF)}$	$V_{EN} = 0V$, $V_D = 0V$, $f = 1MHz$	Room	-	160	-	pF
		DG406	Room	-	80	-
Drain ON Capacitance, $C_{D(ON)}$	$V_{EN} = 5V$, $V_D = 0V$, $f = 1MHz$	Room	-	180	-	pF
		DG407	Room	-	90	-
POWER SUPPLIES						
Positive Supply Current, I_+	$V_{EN} = V_A = 0V$ or 5V Stand By	Room	-	13	30	μA
		Full	-	-	75	μA
Negative Supply Current, I_-		Room	-1	-0.01	-	μA
		Full	-10	-	-	μA
Positive Supply Current, I_+	$V_{EN} = 2.4V$, $V_A = 0V$	Room	-	-0.01	100	μA
		Full	-	-	200	μA
Negative Supply Current, I_-		Room	-1	-	-	μA
		Full	-10	-	-	μA

Electrical Specifications (Single Supply) Test Conditions: $V_+ = 12V$, $V_- = 0V$, $V_{AL} = 0.8V$, $V_{AH} = 2.4V$. Unless Otherwise Specified

PARAMETER	TEST CONDITIONS	(NOTE 3) TEMP	D SUFFIX -40°C TO 85°C			UNITS
			(NOTE 4) MIN	(NOTE 5) TYP	(NOTE 4) MAX	
DYNAMIC CHARACTERISTICS						
Switching Time of Multiplexer, t_{TRANS}	$V_{S1} = 8V$, $V_{S8} = 0V$, $V_{IN} = 2.4V$	Room	-	300	450	ns

DG406, DG407

Electrical Specifications (Single Supply) Test Conditions: $V_+ = 12V$, $V_- = 0V$, $V_{AL} = 0.8V$, $V_{AH} = 2.4V$, Unless Otherwise Specified (Continued)

PARAMETER	TEST CONDITIONS	(NOTE 3) TEMP	D SUFFIX -40°C TO 85°C			UNITS
			(NOTE 4) MIN	(NOTE 5) TYP	(NOTE 4) MAX	
Enable Turn-ON Time, $T_{ON(EN)}$	$V_{INH} = 2.4V$, $V_{INL} = 0V$, $V_{S1} = 5V$	Room	-	250	600	ns
Enable Turn-OFF Time, $T_{OFF(EN)}$		Room	-	150	300	ns
Charge Injection, Q	$C_L = 1nF$, $V_S = 6V$, $R_S = 0\Omega$	Room	-	20	-	pC
ANALOG SWITCH						
Analog Signal Range, V_{ANALOG}		Full	0	-	12	V
Drain-Source ON-Resistance, $r_{DS(ON)}$	$V_D = 3V, 10V$, $I_S = -1mA$ (Note 6)	Room	-	90	120	Ω
$r_{DS(ON)}$ Matching Between Channels (Note 7), $\Delta r_{DS(ON)}$		Room	-	5	-	%
Source Off Leakage Current, $I_{S(OFF)}$	$V_{EN} = 0V$, $V_D = 10V$ or $0.5V$, $V_S = 0.5V$ or $10V$	Room	-	0.01	-	nA
Drain Off Leakage Current, $I_{D(OFF)}$ DG406		Room	-	0.04	-	nA
DG407		Room	-	0.04	-	nA
Drain On Leakage Current, $I_{D(ON)}$ DG406	$V_S = V_D = \pm 10V$ (Note 6)	Room	-	0.04	-	nA
DG407		Room	-	0.04	-	nA
POWER SUPPLIES						
Positive Supply Current (I_+)	$V_{EN} = 0V$ or $5V$, $V_A = 0V$ or $5V$	Room	-	13	30	μA
		Full	-	13	75	μA
Negative Supply Current (I_-)		Room	-1	-0.01	-	μA
		Full	-5	-0.01	-	μA

NOTES:

3. Room = 25°C, Cold and Hot = as determined by the operating temperature suffix.
4. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this data sheet.
5. Typical values are for Design Aid Only, not guaranteed nor production tested.
6. Sequence each switch ON.
7. $\Delta r_{DS(ON)} = r_{DS(ON)} (\text{Max}) - r_{DS(ON)} (\text{Min}) + r_{DS} \text{ average}$
8. Worst case isolation occurs on channel 8B due to proximity to the drain pin.

Test Circuits and Waveforms

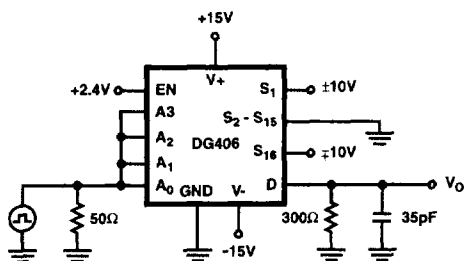


FIGURE 1A.

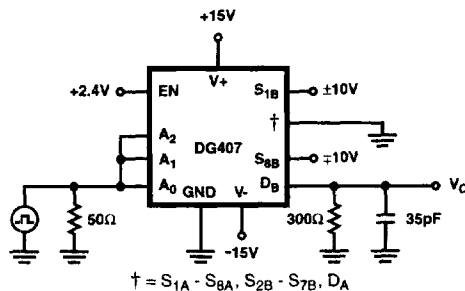


FIGURE 1B.

Test Circuits and Waveforms (Continued)

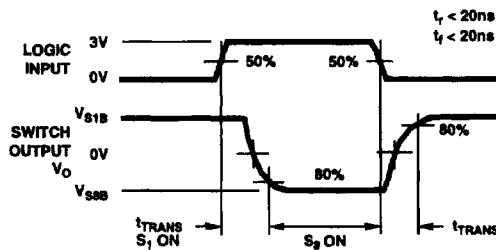


FIGURE 1C.

FIGURE 1. TRANSITION TIME

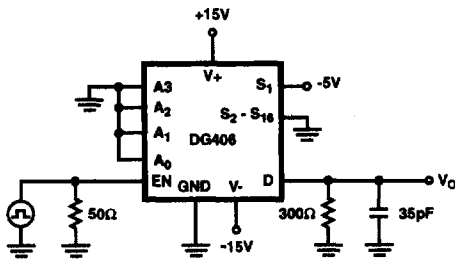


FIGURE 2A.

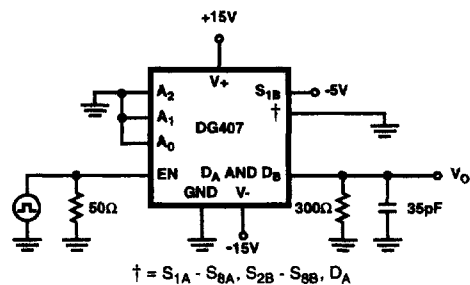


FIGURE 2B.

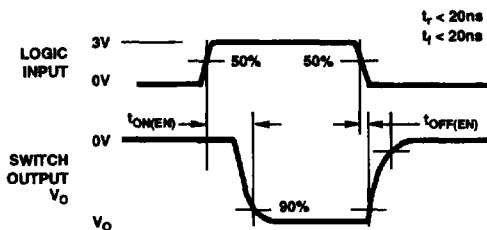


FIGURE 2C.

FIGURE 2. ENABLE SWITCHING TIME

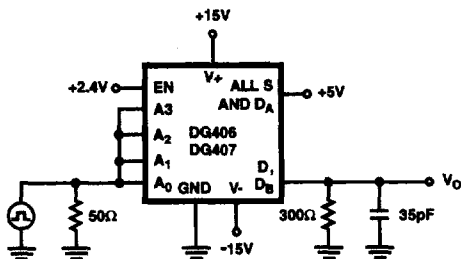


FIGURE 3A.

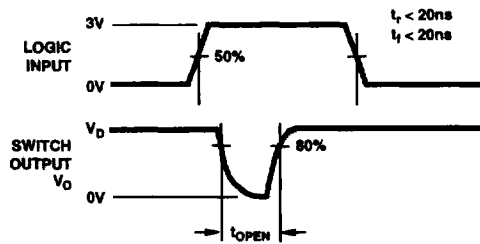


FIGURE 3B.

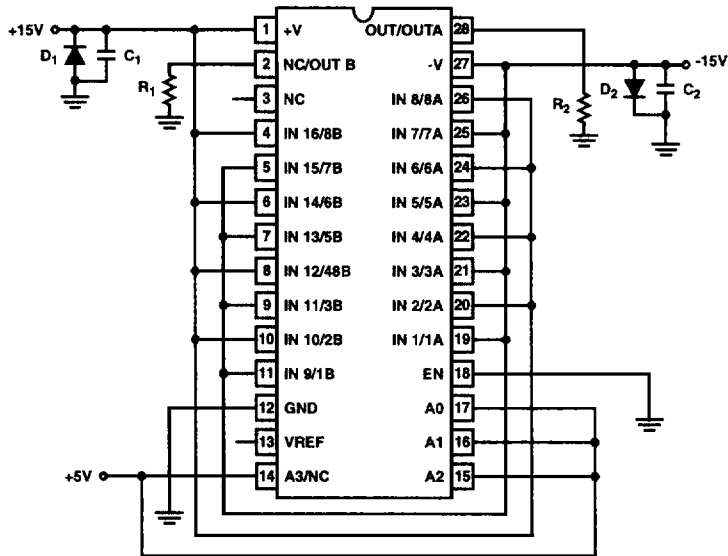
FIGURE 3. BREAK-BEFORE-MAKE INTERVAL

DG406, DG407

Burn-In Circuit

CERDIP/SOIC BURN-IN SCHEMATIC

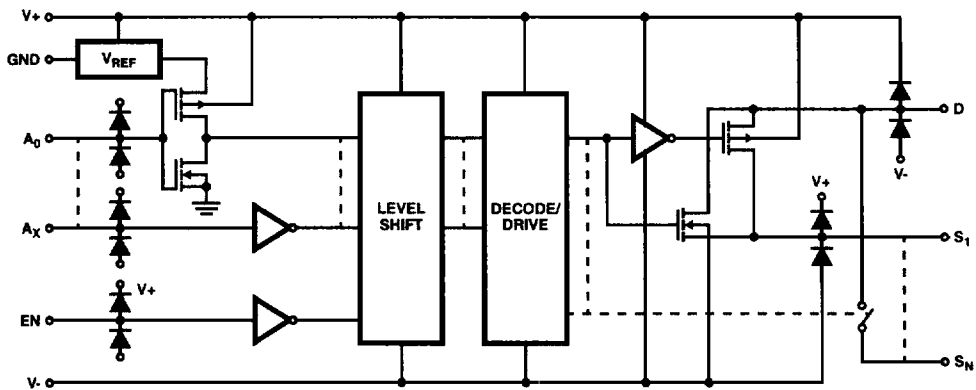
DG406/407EY/EJ



NOTE:

R₁, R₂ = 10kΩ ±5%, 1/2W or 1/4W (Per Socket)
 C₁, C₂ = 0.01μF (Min, Per Socket) or 0.1μF (Min, Per Row)
 D₁, D₂ = IN402 (or Equivalent, Per Board)

Schematic Diagram (Typical Channel)



Typical Performance Curves

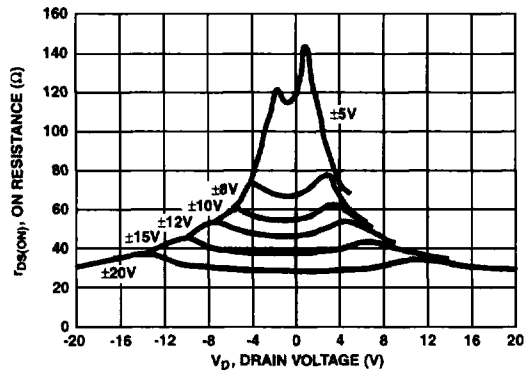


FIGURE 4. $r_{DS(ON)}$ vs V_D AND SUPPLY

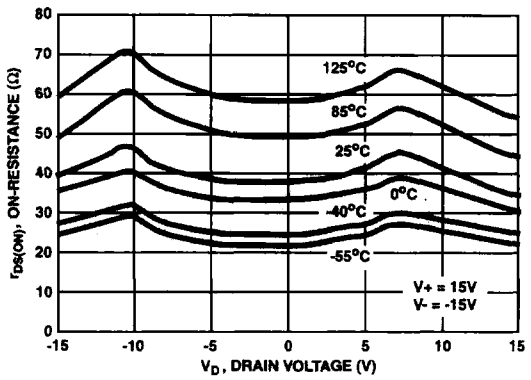


FIGURE 5. $r_{DS(ON)}$ vs V_D AND TEMPERATURE

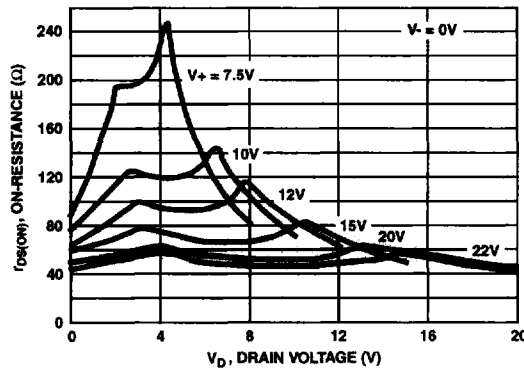


FIGURE 6. $r_{DS(ON)}$ vs V_D AND SUPPLY

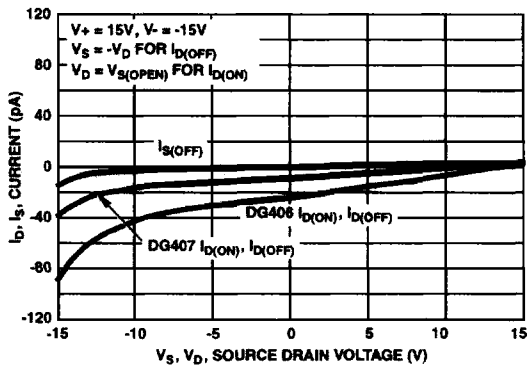


FIGURE 7. I_D, I_S LEAKAGE CURRENTS vs ANALOG VOLTAGE

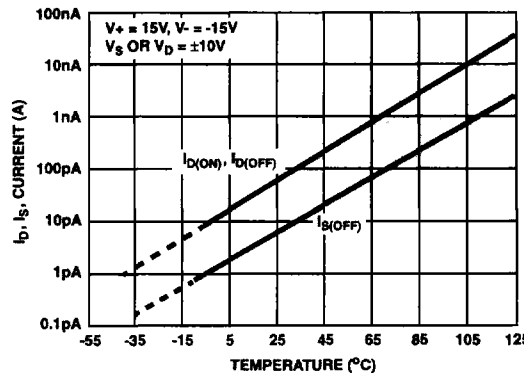


FIGURE 8. I_D, I_S LEAKAGE vs TEMPERATURE

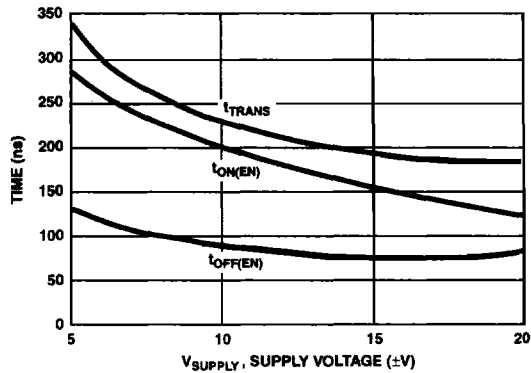


FIGURE 9. SWITCHING TIMES vs BIPOLAR SUPPLIES

Typical Performance Curves (Continued)

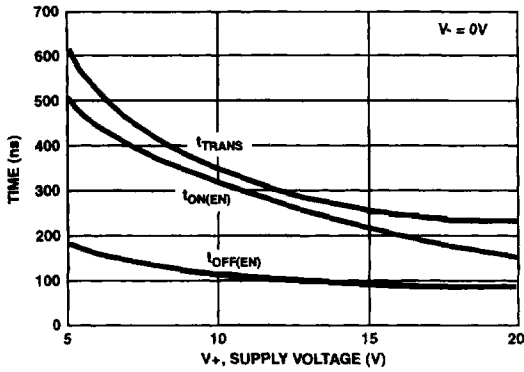


FIGURE 10. SWITCHING TIMES vs SINGLE SUPPLY

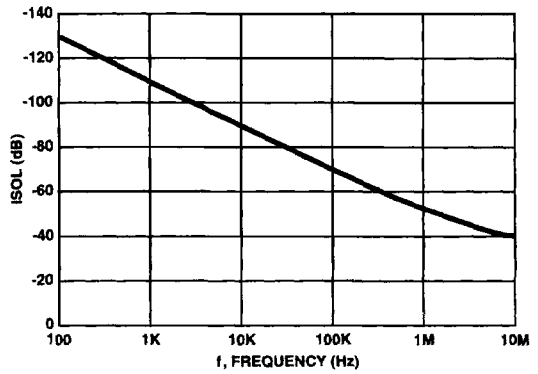


FIGURE 11. OFF-ISOLATION vs FREQUENCY

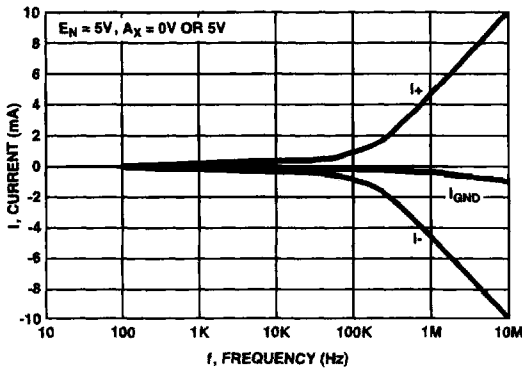


FIGURE 12. SUPPLY CURRENTS vs SWITCHING FREQUENCY

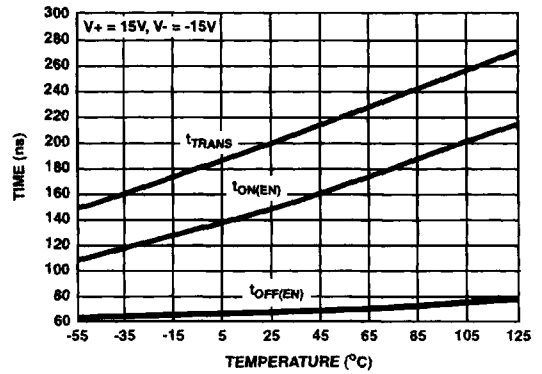


FIGURE 13. t_{ON}/t_{OFF} vs TEMPERATURE

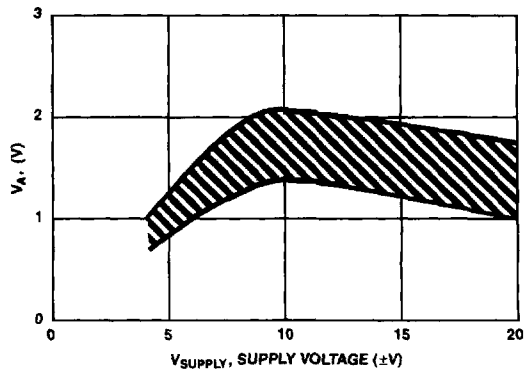


FIGURE 14. SWITCHING THRESHOLD vs SUPPLY VOLTAGE

DG406, DG407

Die Characteristics

DIE DIMENSIONS:

2490 μ m x 4560 μ m x 485 μ m \pm 25 μ m

METALLIZATION:

Type: SiAl
Thickness: 12k Å \pm 1k Å

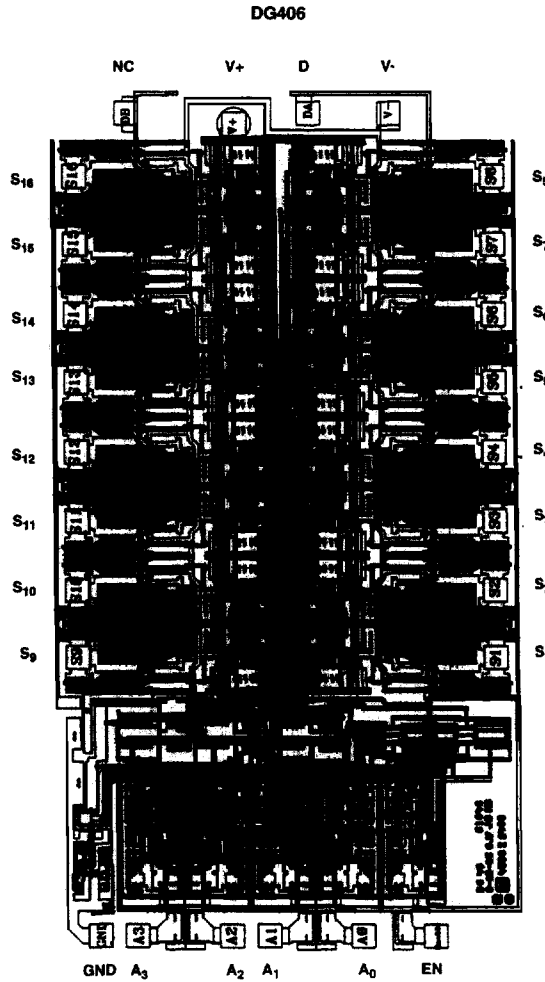
PASSIVATION:

Type: Nitride
Thickness: 8k Å \pm 1k Å

WORST CASE CURRENT DENSITY:

9.1 x 10⁴ A/cm²

Metallization Mask Layout



DG406, DG407

Die Characteristics

DIE DIMENSIONS:

2490 μm x 4560 μm x 485 μm \pm 25 μm

METALLIZATION:

Type: SiAl

Thickness: 12k Å \pm 1k Å

PASSIVATION:

Type: Nitride

Thickness: 8k Å \pm 1k Å

WORST CASE CURRENT DENSITY:

9.1 x 10⁴ A/cm²

Metallization Mask Layout

DG407

